Docket No.: 2013P135

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re the Application of:	
SEONG HYUN KIM, ET AL.	Art Group
Application No.:	Examiner:
Filed:	
For: Vertical Structure Thin Film Transistor	

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted concurrently with the Utility Application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

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The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

Date: ______(1/25/03

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

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Telephone: (310) 207-3800

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known		
		Application Number		
		Filing Date		
		First Named Inventor	Seong Hyun Kim	
		Art Unit		
		Examiner Name		
Sheet	of	Attorney Docket Number	2013P135	

U.S. PATENT DOCUMENTS					
		Document Number	Publication Date		Person Column Line Ma
Examiner Initials*	Cite No.1	Number - Kind Code ² (if known)	or Issue Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US-			
		US-			· · · · · · · · · · · · · · · · · · ·
		US-			

	FOREIGN PATENT DOCUMENTS						
Examiner Cite No.1	Cite	Foreign Patent Document			Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
	No.1	Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document		T⁵	
		P2001-0034186	04-25-2001	Thin Film Electronics ASA			
					_		
			-				

Examiner	 Date	
Signature	Considered	

^{*}Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication.

¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Substitute for form 1449A/PTO			Complete if Known	
		Application Number		
INFORMATION DISCLOSURE		Filing Date		
STATEMENT BY APPLICANT (use as many sheets as necessary)		First Named Inventor	Seong Hyun Kim	
		Art Unit		
		Examiner Name		
Sheet	of	Attorney Docket Number	2013P135	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
		"Vertical p-type high-mobility heterojunction metal-oxide-semiconductor field-effect transistors", X. Chen, et al., 2001 American Institute of Physics	
		Applied Physics Letters, "Conductance quantization in nanoscale vertical structure silicon field-effect trnsistors witha wrap gate", K. Nishiguchi, et al., 2000 American Institute of Physics	
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Examiner | Date | Considered |

Based on PTO/SB/08B (08-03) as modified by Blakely, Solokoff, Taylor & Zafman (wtr) 08/11/2003. Send To: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

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